

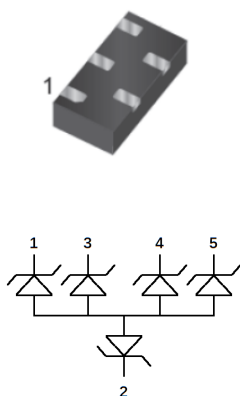
Features

- ◆ Small package: DFN2010-5L
- ◆ Ultra low capacitance: 0.2pF typical
- ◆ Ultra low leakage: nA level
- ◆ Low operating voltage: 5V
- ◆ Low clamping voltage
- ◆ 2-pin leadless package
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ±15kV
 - Contact discharge: ±8kV
 - IEC61000-4-5 (Lightning) 3A (8/20μs)
- ◆ RoHS Compliant

Description

The ESDA5B0M0D8 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ESDA5B0M0D8 has an ultra-low capacitance with a typical value at 0.2pF, and complies with the IEC 61000-4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. It is assembled into an ultra-small lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make ESDA5B0M0D8 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Circuit Diagram



Applications

- ◆ Smart phones
- ◆ Display Ports
- ◆ MDDI Ports
- ◆ USB Ports
- ◆ Digital Video Interface (DVI)
- ◆ PCI Express and Serial SATA Ports

Absolute Maximum Ratings : ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

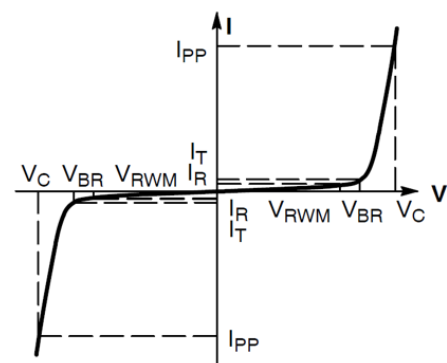
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	60	W
Peak Pulse Current (8/20 μs)	IPP	3	A
ESD per IEC 61000-4-2 (Air)	VESD	± 15	kV
ESD per IEC 61000-4-2 (Contact)		± 8	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics : ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

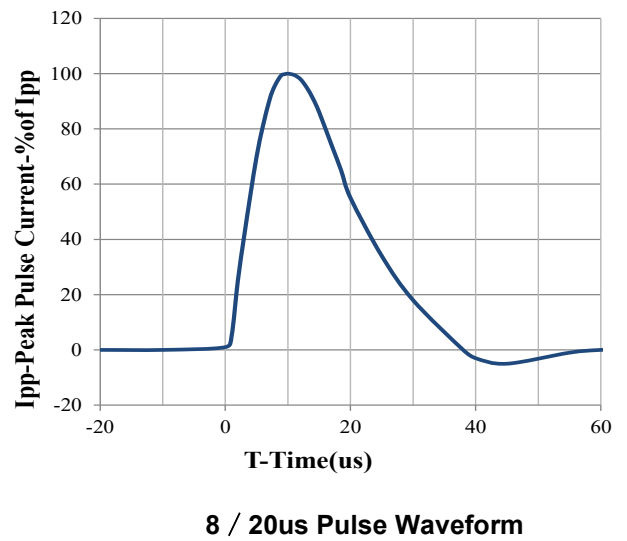
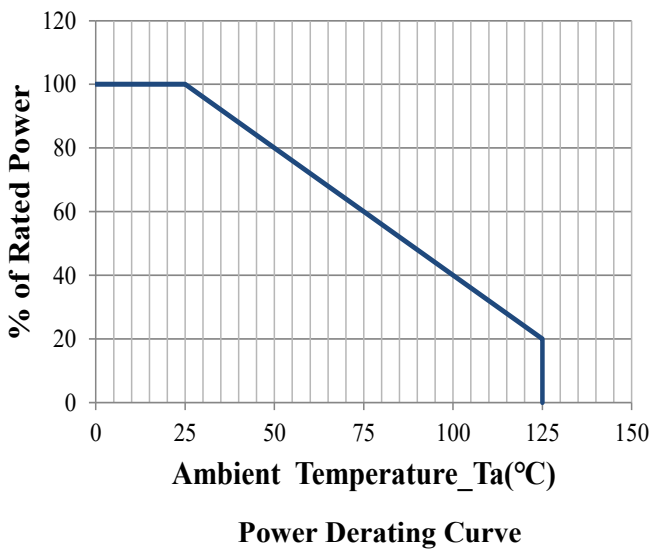
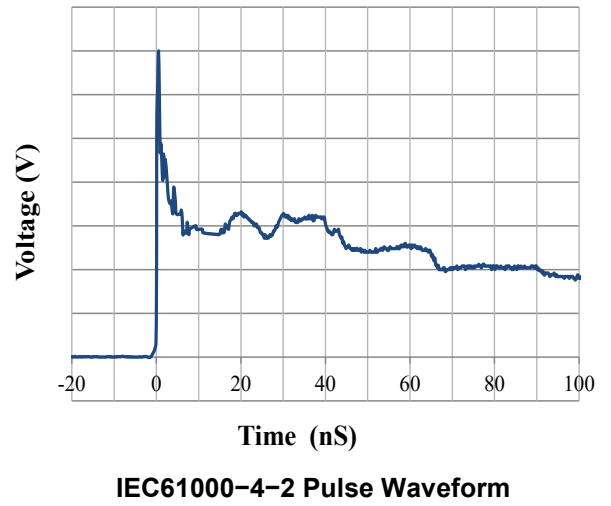
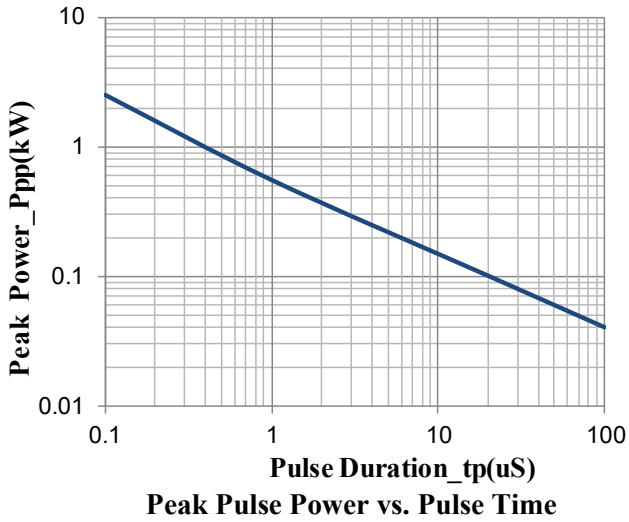
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$, I/O-GND	7.0	8.0	9.0	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$, I/O-I/O	7.0	8.0	9.0	V
Reverse Leakage Current	I_R	$V_{RWM} = 5\text{V}$		5	100	nA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 / 20 μs pulse), I/O-GND		10	12	V
Clamping Voltage	V_C	$I_{PP} = 3\text{A}$ (8 / 20 μs pulse), I/O-GND		17	20	V
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 / 20 μs pulse), I/O-I/O		10	12	V
Clamping Voltage	V_C	$I_{PP} = 3\text{A}$ (8 / 20 μs pulse), I/O-I/O		17	20	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$, I/O-GND		0.2	0.3	pF
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$, I/O-I/O		0.2	0.3	pF

Portion Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}

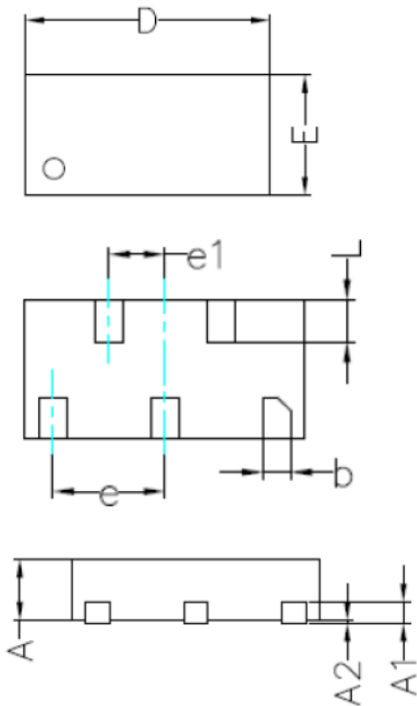

Bi-Directional TVS

Typical Characteristics: (T_c=25°C unless otherwise noted)



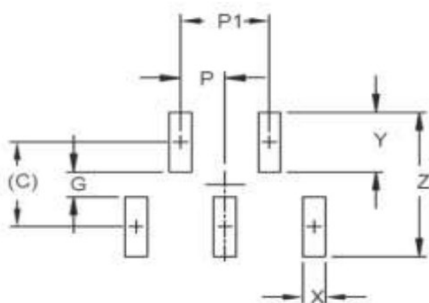
Package Dimension

DFN1006-2(0402) Package Outline



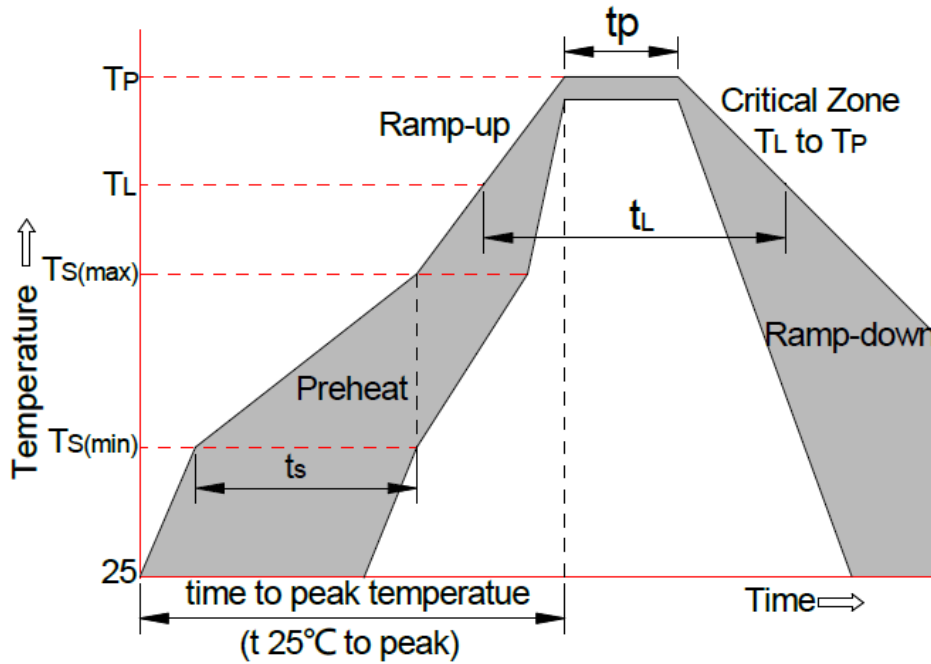
SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.40	0.50	0.55	0.016	0.020	0.022
A1	0.15REF.			0.006REF.		
A2	0.00	0.02	0.05	0.00	0.0008	0.002
D	1.95	2.00	2.05	0.077	0.079	0.081
E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.25	0.30	0.35	0.01	0.012	0.014
b	0.15	0.20	0.25	0.006	0.008	0.01
e1	0.40BSC			0.016BSC		
e	0.80BSC			0.032BSC		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.85	0.033
G	0.25	0.01
P	0.40	0.016
P1	0.80	0.032
X	0.20	0.008
Y	0.60	0.024
Z	1.45	0.057

Soldering Parameters



Reflow Condition		Pb-Free Assembly
Pre-heat	-Temperature Min (Ts (min))	+150°C
	-Temperature Max (Ts (max))	+200°C
	-Time (Min to Max) (ts)	60-180 secs
Average ramp up rate(Liquid us Temp (TL) to peak)		3°C/sec. Max
Ts (max) to TL-Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature (TL) (Liquid us)	+217°C
	-Temperature (tL)	60-150 secs
Peak Temp (Tp)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (tp)		30 secs. Max
Ramp-down Rate		6 °C/secs. Max
xTime 25°C to Peak Temp (TP)		8 min. Max
Do not exceed		+260°C